

Dual N-Channel OptiMOS™ MOSFET

Features

- Dual N-channel OptiMOS™ MOSFET
- Optimized for high performance Buck converter
- Logic level (4.5V rated)
- 100% avalanche tested
- Qualified according to JEDEC¹⁾ for target applications
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- Integrated monolithic Schottky-like diode



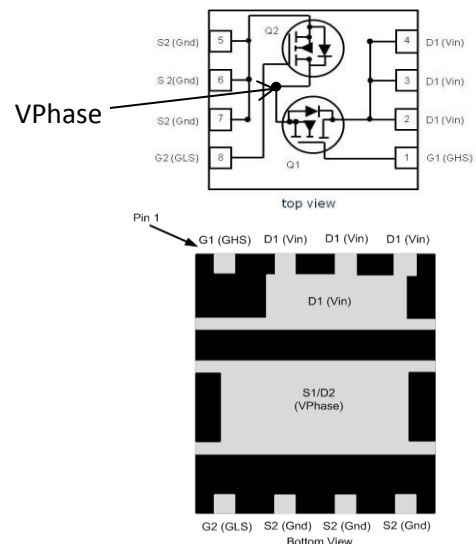
Type	Package	Marking
BSC0910NDI	PG-TISON-8	0910NDI

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified ²⁾

Parameter	Symbol	Conditions	Value		Unit
			Q1	Q2	
Continuous drain current	I_D	$T_C=70\text{ °C}$, $V_{GS}=10\text{ V}$	40	40	A
		$T_A=25\text{ °C}$, $V_{GS}=4.5\text{ V}^{3)}$	16	31	
		$T_A=70\text{ °C}$, $V_{GS}=4.5\text{ V}^{3)}$	13	25	
		$T_A=25\text{ °C}$, $V_{GS}=10\text{ V}^{4)}$	11	22	
Pulsed drain current ⁵⁾	$I_{D,pulse}$	$T_C=70\text{ °C}$	160	160	
Avalanche energy, single pulse	E_{AS}	Q1: $I_D=20\text{ A}$, Q2: $I_D=20\text{ A}$, $R_{GS}=25\text{ }\Omega$	12	80	mJ
Gate source voltage	V_{GS}		± 20		V
Power dissipation	P_{tot}	$T_A=25\text{ °C}^{2)}$	2.5	2.5	W
		$T_A=25\text{ °C}$, minimum footprint ⁴⁾	1.0	1.0	
Operating and storage temperature	T_j, T_{stg}		-55 ... 150		°C
IEC climatic category; DIN IEC 68-1			55/150/56		

Product Summary

		Q1	Q2	
V_{DS}		25	25	V
$R_{DS(on),max}$	$V_{GS}=10\text{ V}$	4.6	1.2	m Ω
	$V_{GS}=4.5\text{ V}$	5.9	1.6	
I_D		40	40	A



Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	Q1	R_{thJC}		-	-	4.5	K/W
	Q2			-	-	1.5	
Thermal resistance, junction - ambient ¹⁾	Q1	R_{thJA}	6 cm ² cooling area ³⁾	-	-	50	
	Q2			-	-		
	Q1		minimal footprint, steady state ⁴⁾	-	-	125	
	Q2			-	-		

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	Q1	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=10\text{ mA}$	25	-	-	V
	Q2						
Breakdown voltage temperature coefficient	Q1	$dV_{(BR)DSS}/dT_j$	$I_D=10\text{ mA}$, referenced to 25 °C	-	15	-	mV/K
	Q2						
Gate threshold voltage	Q1	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$	1	-	2	V
	Q2						
Zero gate voltage drain current	Q1	I_{DSS}	$V_{DS}=20\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	-	1	μA
	Q2			-	-	500	
	Q1		$V_{DS}=20\text{ V}, V_{GS}=0\text{ V}, T_j=150\text{ °C}$	-	-	0.1	mA
	Q2			-	3	-	
Gate-source leakage current	Q1	I_{GSS}	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	-	100	nA
	Q2						
Drain-source on-state resistance	Q1	$R_{DS(on)}$	$V_{GS}=4.5\text{ V}, I_D=25\text{ A}$	-	4.7	5.9	m Ω
	Q2			-	1.25	1.6	
	Q1		$V_{GS}=10\text{ V}, I_D=25\text{ A}$	-	3.5	4.6	
	Q2			-	0.9	1.2	
Gate resistance	Q1	R_G		0.4	0.8	1.6	Ω
	Q2			0.4	0.7	1.4	
Transconductance	Q1	g_{fs}	$ V_{DS} >2 I_D R_{DS(on)max}, I_D=30\text{ A}$	42	84	-	S
	Q2			85	170	-	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	Q1	C_{iss}	$V_{GS}=0\text{ V},$ $V_{DS}=12\text{ V}, f=1\text{ MHz}$	-	760	1000	pF
	Q2			-	3400	4500	
Output capacitance	Q1	C_{oss}		-	370	500	
	Q2			-	1700	2300	
Reverse transfer capacitance	Q1	C_{rss}		-	35	-	
	Q2			-	150	-	
Turn-on delay time	Q1	$t_{d(on)}$	$V_{DD}=12\text{ V},$ $V_{GS}=10\text{ V}, R_G=1.6\text{ }\Omega,$ $I_D=30\text{ A}$	-	2.4	-	ns
	Q2			-	5.6	-	
Rise time	Q1	t_r		-	3.6	-	
	Q2			-	5.6	-	
Turn-off delay time	Q1	$t_{d(off)}$		-	13	-	
	Q2			-	28	-	
Fall time	Q1	t_f		-	2.4	-	
	Q2			-	4.1	-	

Gate Charge Characteristics

Gate to source charge	Q1	Q_{gs}	$V_{DD}=12\text{ V},$ $I_D=30\text{ A},$ $V_{GS}=0\text{ to }4.5\text{ V}$	-	1.9	2.5	nC
Gate to drain charge		Q_{gd}		-	1.2	1.8	
Switching charge		Q_g		-	5.0	6.6	
Gate plateau voltage		$V_{plateau}$		-	2.5	-	V
Gate to source charge	Q2	Q_{gs}		-	8.1	10.8	
Gate to drain charge		Q_{gd}		-	5.6	8.4	
Switching charge		Q_g		-	23	30.6	
Gate plateau voltage		$V_{plateau}$		-	2.4	-	
Output charge	Q1	Q_{oss}	$V_{DD}=12\text{ V}, V_{GS}=0\text{ V}$	-	8	10.6	nC
	Q2			-	36	48	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Reverse Diode

Diode continuous forward current	Q1	I_S	$T_C=25\text{ °C}$	-	-	28	A
	Q2			-	-	40	
Diode pulse current	Q1	$I_{S,pulse}$		-	-	160	
	Q2			-	-	160	
Diode forward voltage	Q1	V_{SD}	$V_{GS}=0\text{ V}, I_F=20\text{ A}, T_j=25\text{ °C}$	-	0.87	1	V
	Q2		$V_{GS}=0\text{ V}, I_F=10\text{ A}, T_j=25\text{ °C}$	-	0.56	0.7	
Reverse recovery charge	Q1	Q_{rr}	$V_R=12\text{ V}, I_F=10\text{ A}, di_F/dt=400\text{ A/}\mu\text{s}$	-	5	-	nC
	Q2			-	5	-	nC

¹⁾ J-STD20 and JESD22

²⁾ One transistor active

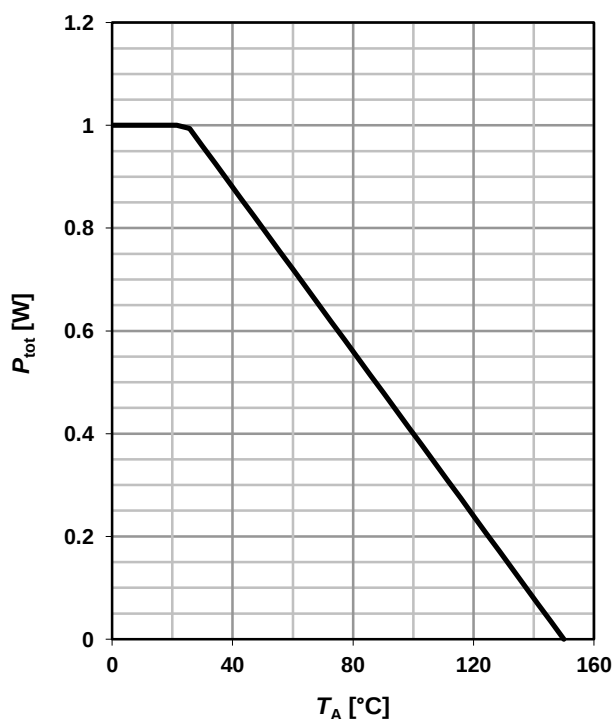
³⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is

⁴⁾ Device mounted on a minimum pad (one layer, 70 μm thick). One transistor active.

⁵⁾ See figure 3 for more detailed information.

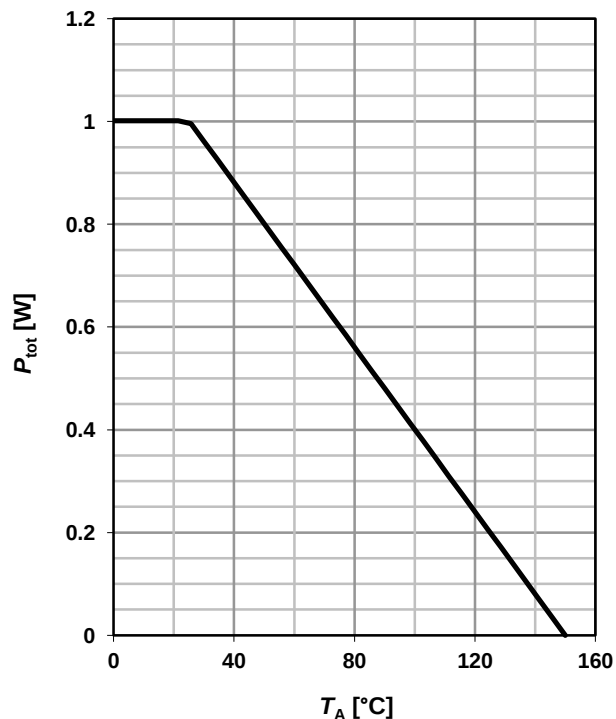
1 Power dissipation (Q1)

$$P_{\text{tot}} = f(T_A)^{(3)}$$



2 Power dissipation (Q2)

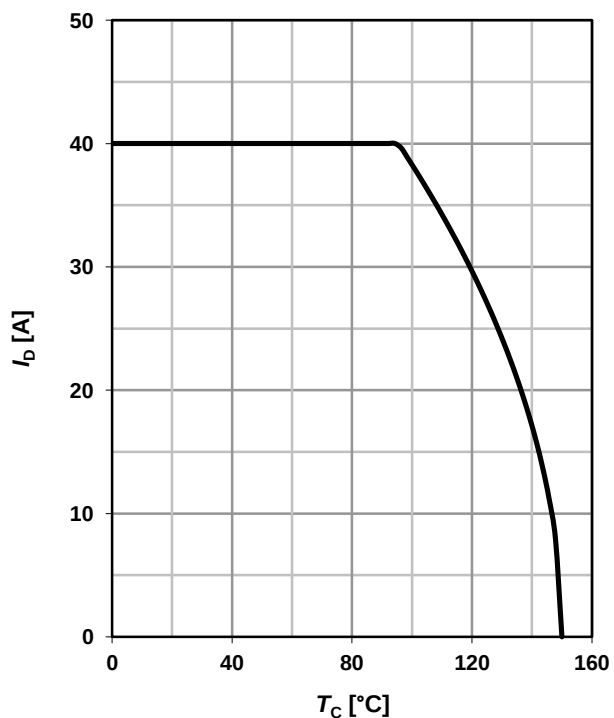
$$P_{\text{tot}} = f(T_A)^{(3)}$$



3 Drain current (Q1)

$$I_D = f(T_C)$$

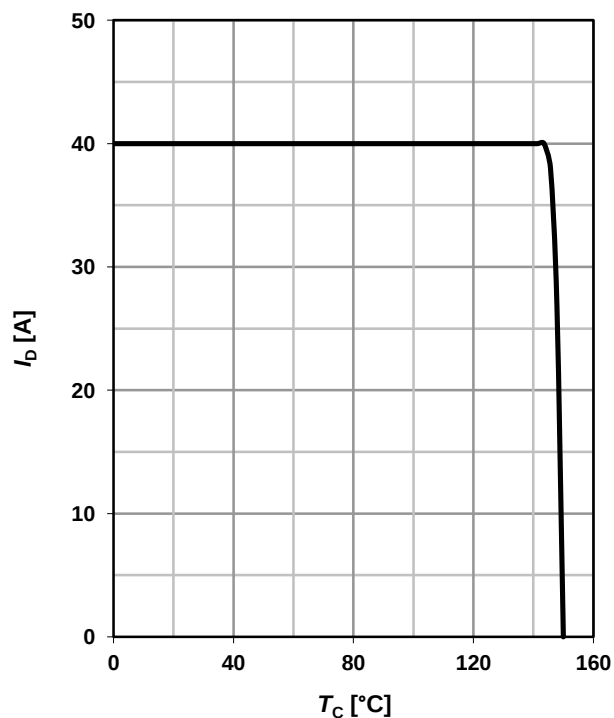
parameter: $V_{GS} \geq 10$ V



4 Drain current (Q2)

$$I_D = f(T_C)$$

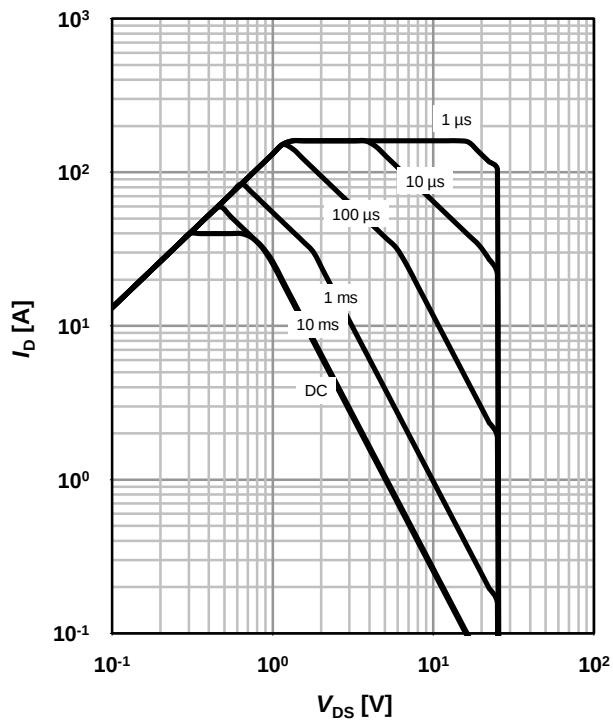
parameter: $V_{GS} \geq 10$ V



5 Safe operating area (Q1)

$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

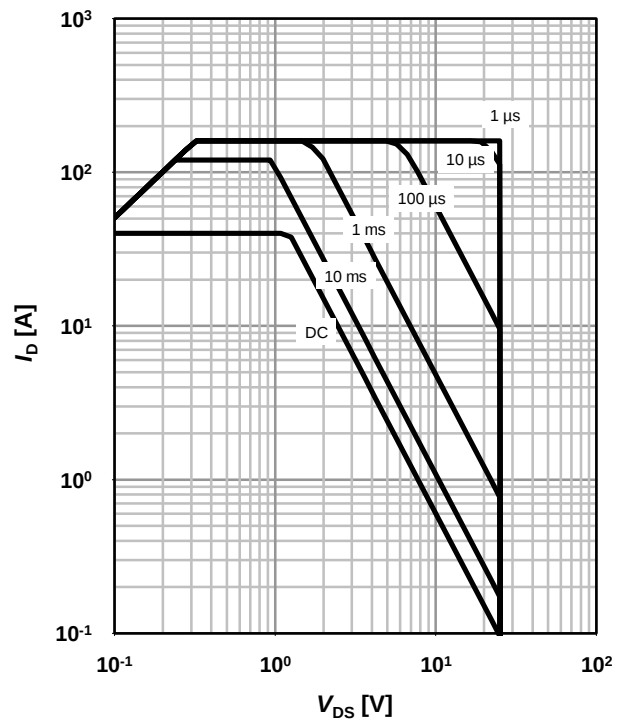
parameter: t_p



6 Safe operating area (Q2)

$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

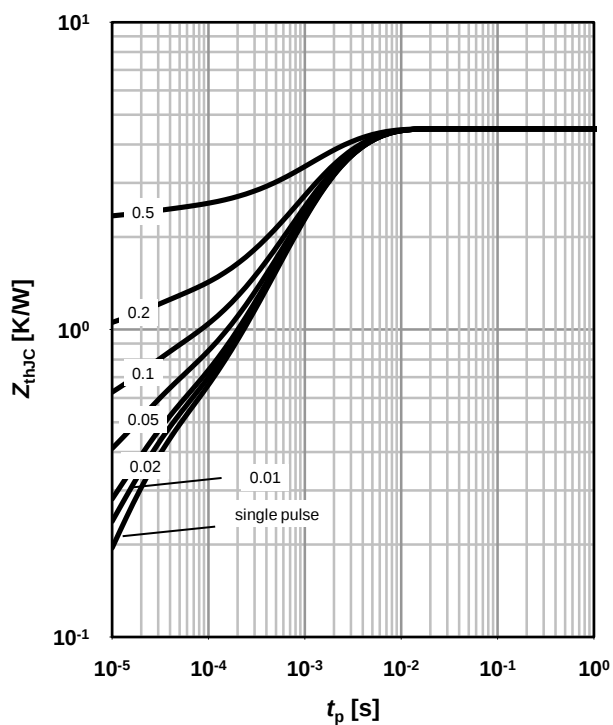
parameter: t_p



7 Max. transient thermal impedance (Q1)

$$Z_{thJC} = f(t_p)$$

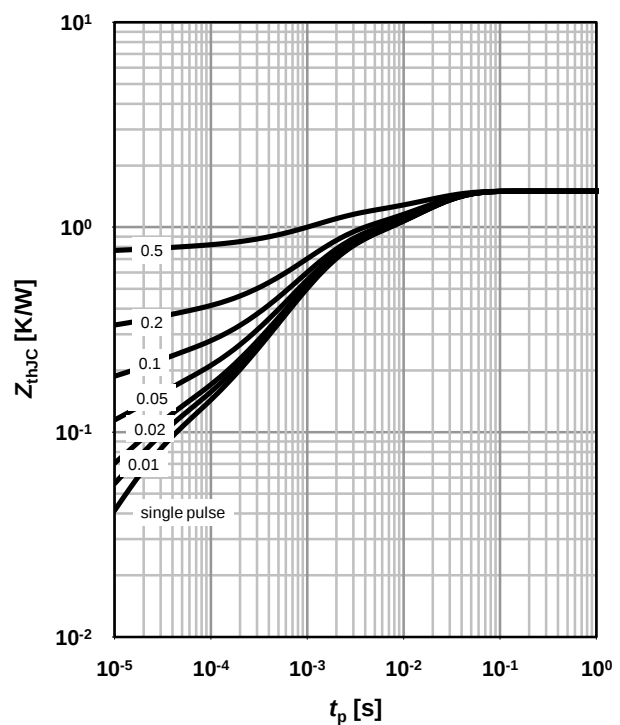
parameter: $D = t_p/T$



8 Max. transient thermal impedance (Q2)

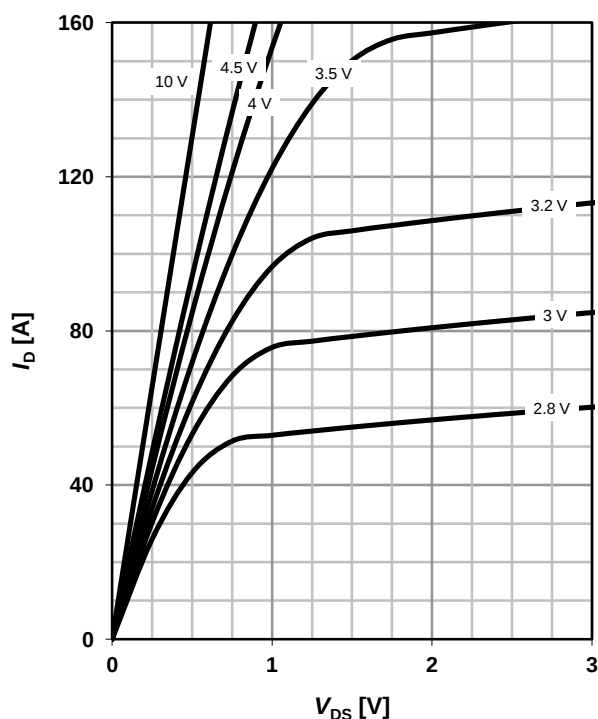
$$Z_{thJC} = f(t_p)$$

parameter: $D = t_p/T$



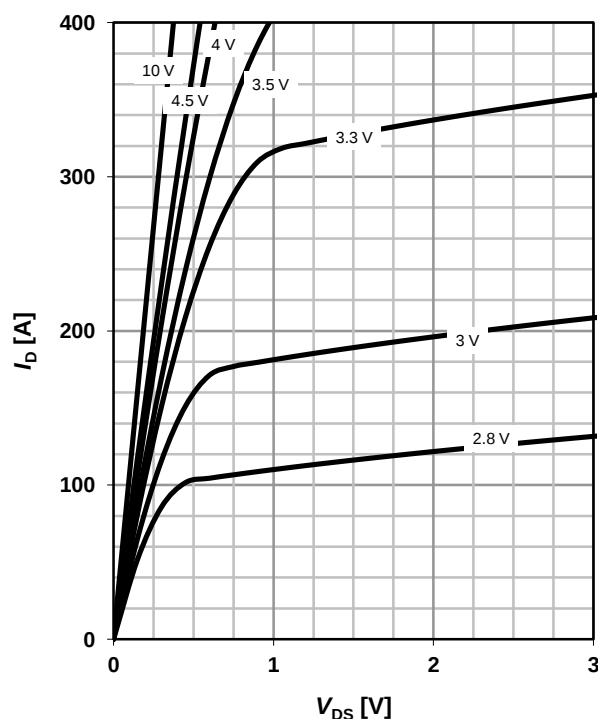
9 Typ. output characteristics (Q1)

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

parameter: V_{GS}


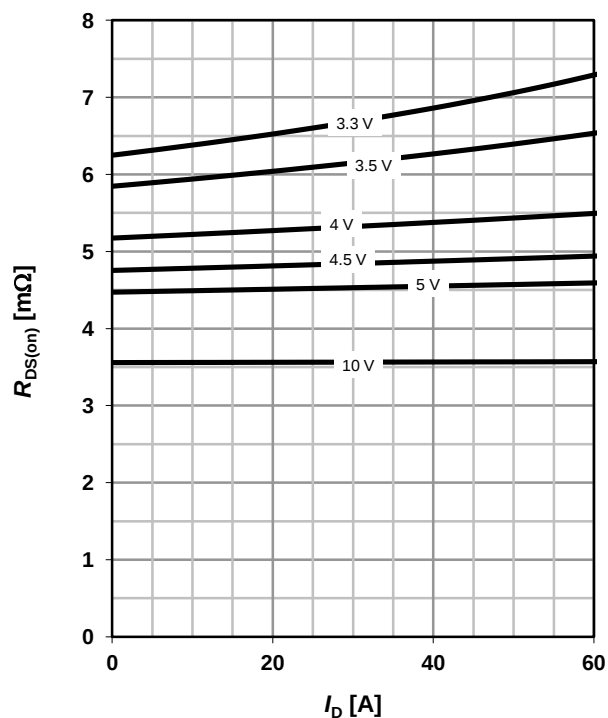
10 Typ. output characteristics (Q2)

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

parameter: V_{GS}


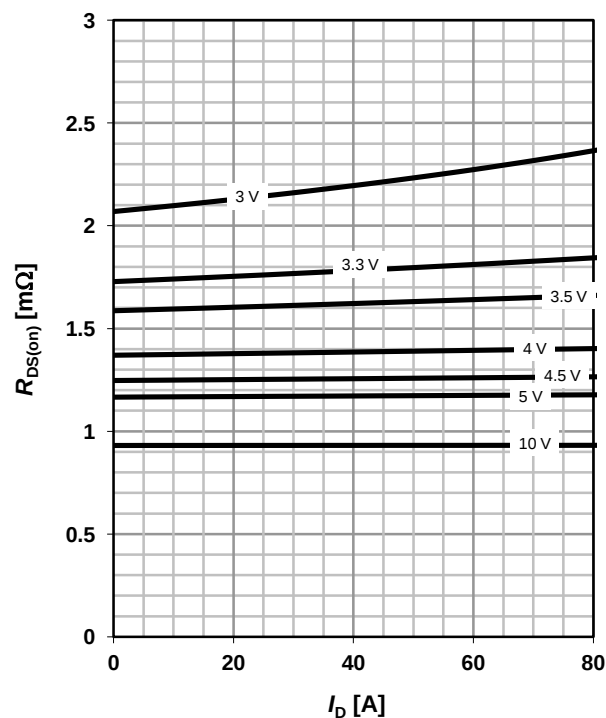
11 Typ. drain-source on resistance (Q1)

 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$

parameter: V_{GS}


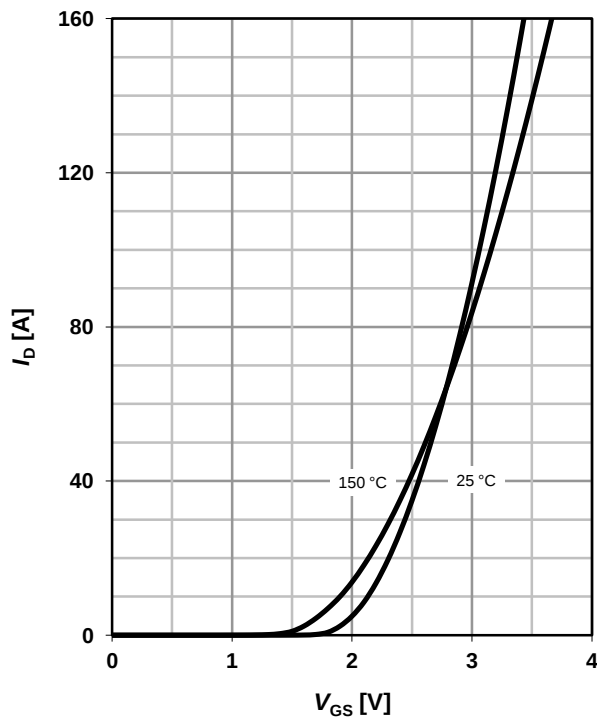
12 Typ. drain-source on resistance (Q2)

 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$

parameter: V_{GS}


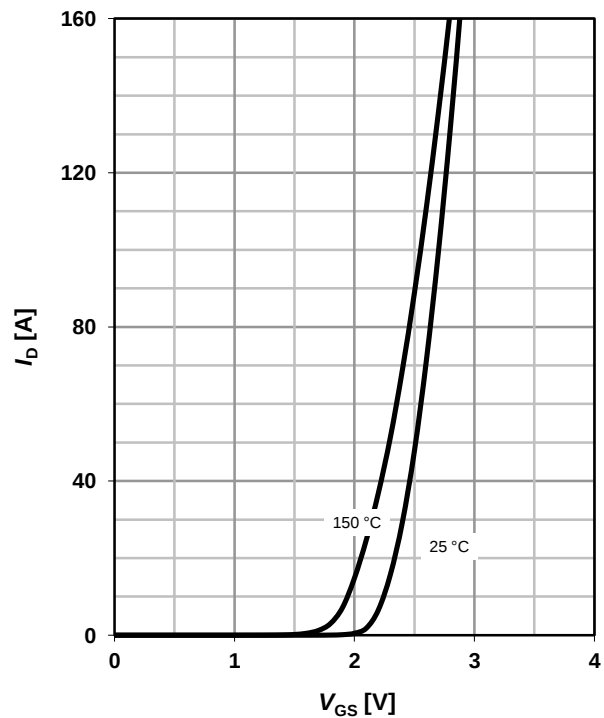
13 Typ. transfer characteristics (Q1)

 $I_D = f(V_{GS}); |V_{DS}| > 2 |I_D| R_{DS(on)max}$

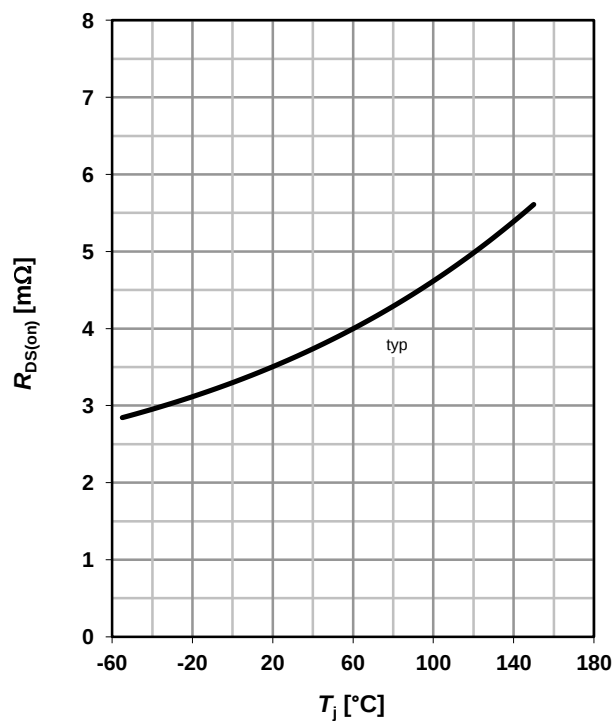
parameter: T_j


14 Typ. transfer characteristics (Q2)

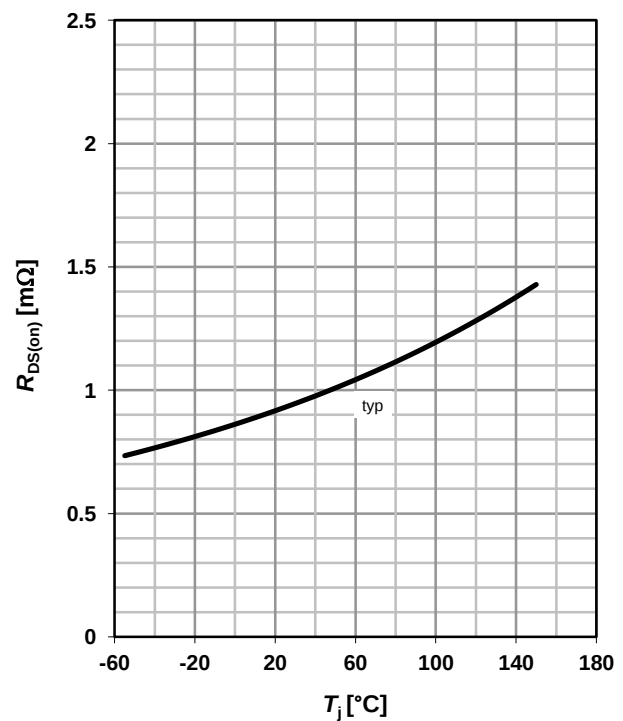
 $I_D = f(V_{GS}); |V_{DS}| > 2 |I_D| R_{DS(on)max}$

parameter: T_j


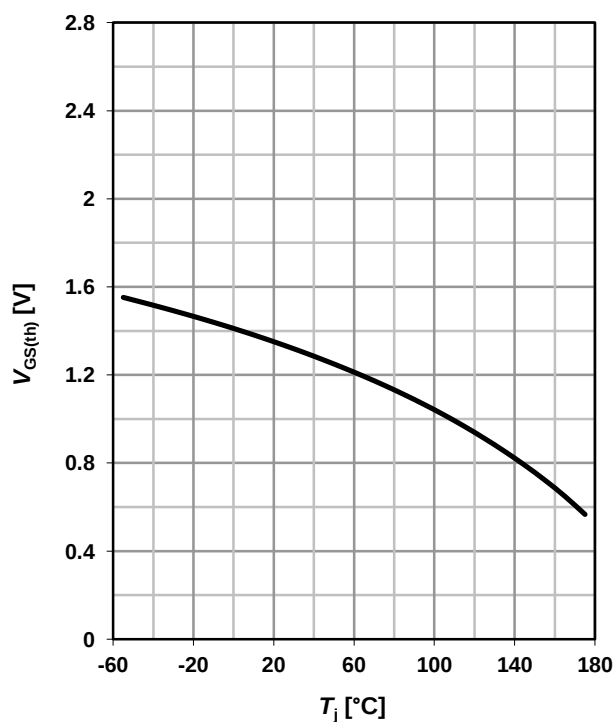
15 Drain-source on-state resistance (Q1)

 $R_{DS(on)} = f(T_j); I_D = 25 \text{ A}; V_{GS} = 10 \text{ V}$


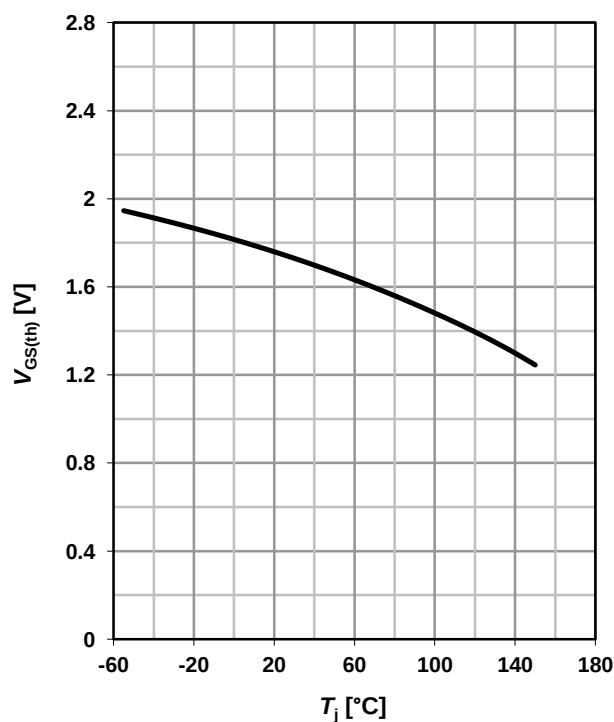
16 Drain-source on-state resistance (Q2)

 $R_{DS(on)} = f(T_j); I_D = 25 \text{ A}; V_{GS} = 10 \text{ V}$


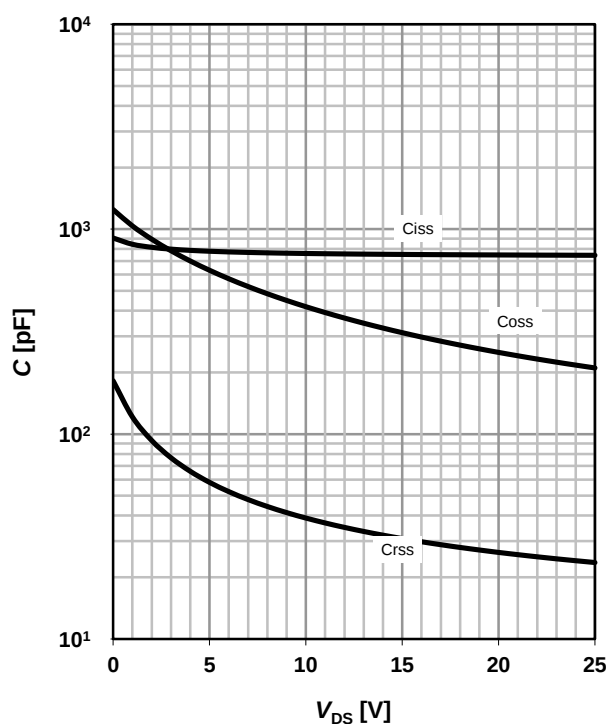
17 Typ. gate threshold voltage (Q1)

 $V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = 250 \mu A$


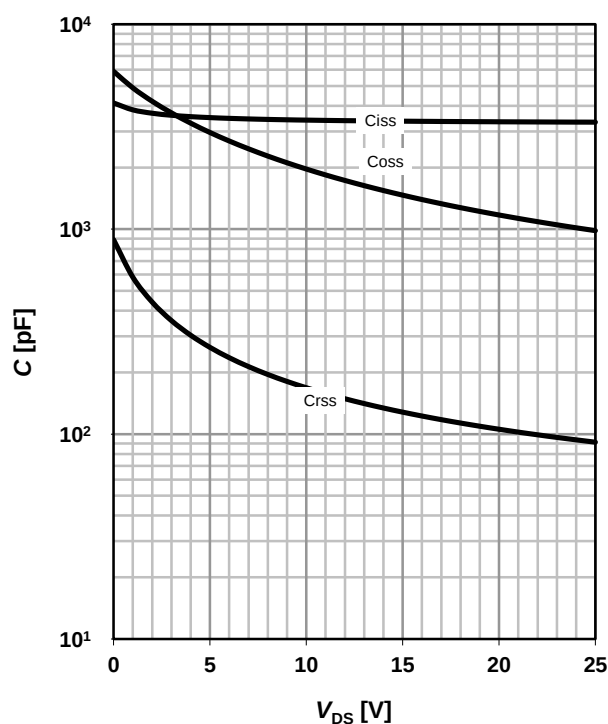
18 Typ. gate threshold voltage (Q2)

 $V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = 10 \text{ mA}$


19 Typ. capacitances (Q1)

 $C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$


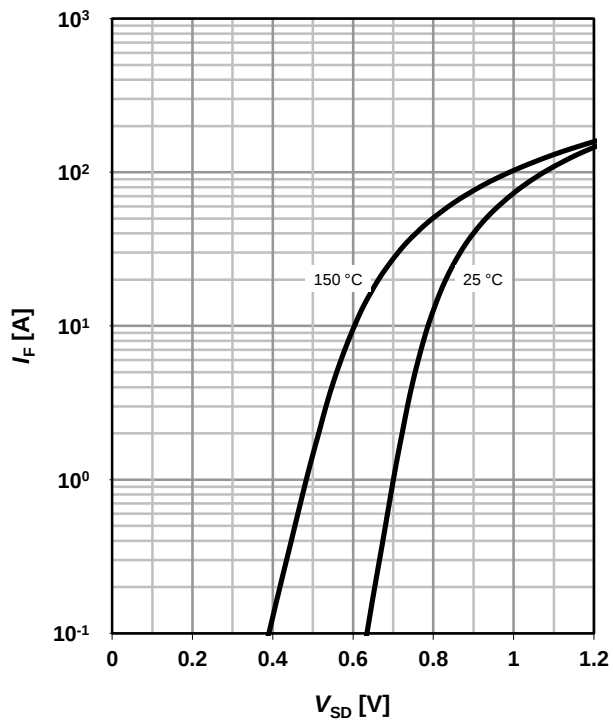
20 Typ. capacitances (Q2)

 $C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$


21 Forward characteristics of reverse diode (Q1)

$$I_F = f(V_{SD})$$

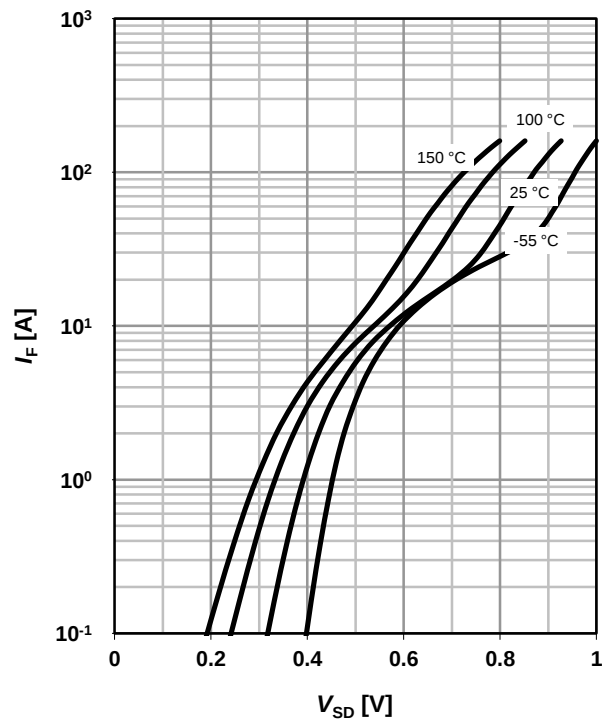
parameter: T_j



22 Forward characteristics of reverse diode (Q2)

$$I_F = f(V_{SD})$$

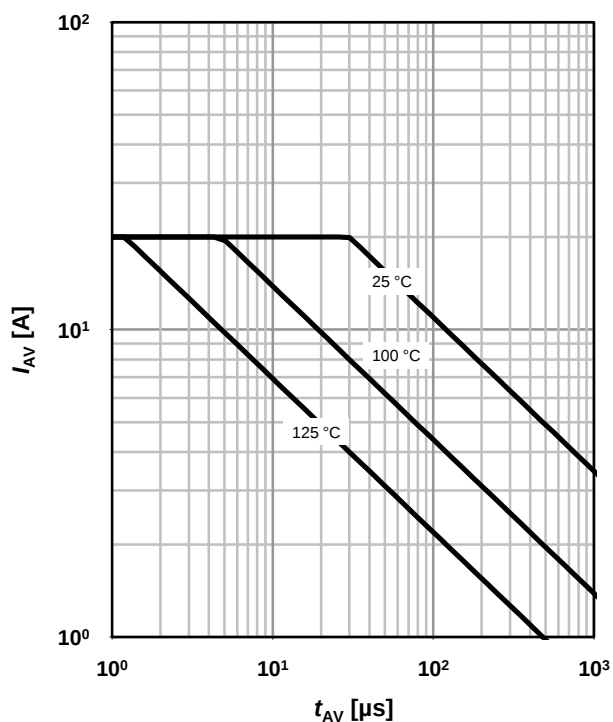
parameter: T_j



23 Avalanche characteristics (Q1)

$$I_{AS} = f(t_{AV}); R_{GS} = 25 \Omega$$

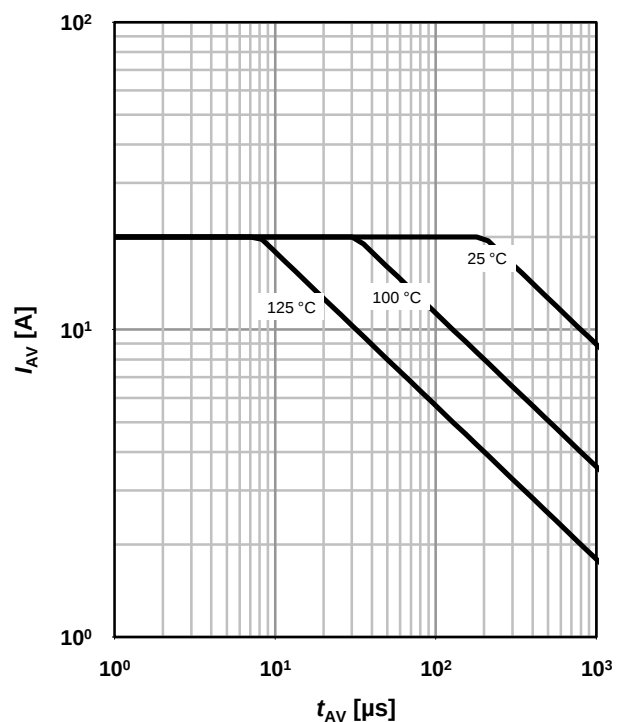
parameter: $T_{j(start)}$



24 Avalanche characteristics (Q2)

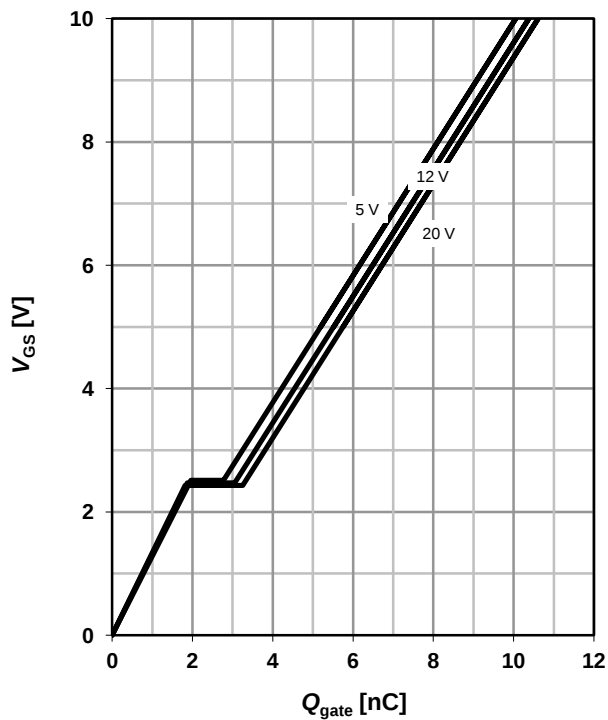
$$I_{AS} = f(t_{AV}); R_{GS} = 25 \Omega$$

parameter: $T_{j(start)}$



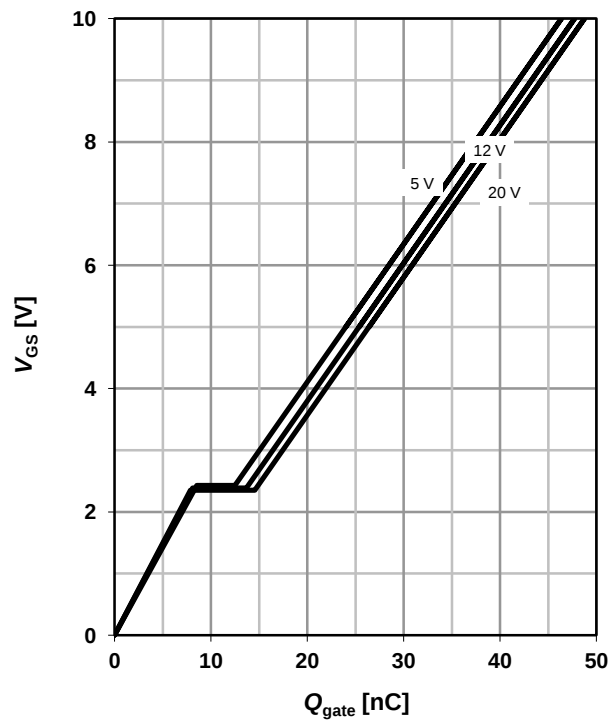
25 Typ. gate charge (Q1)

 $V_{GS}=f(Q_{gate}); I_D=20\text{ A pulsed}$

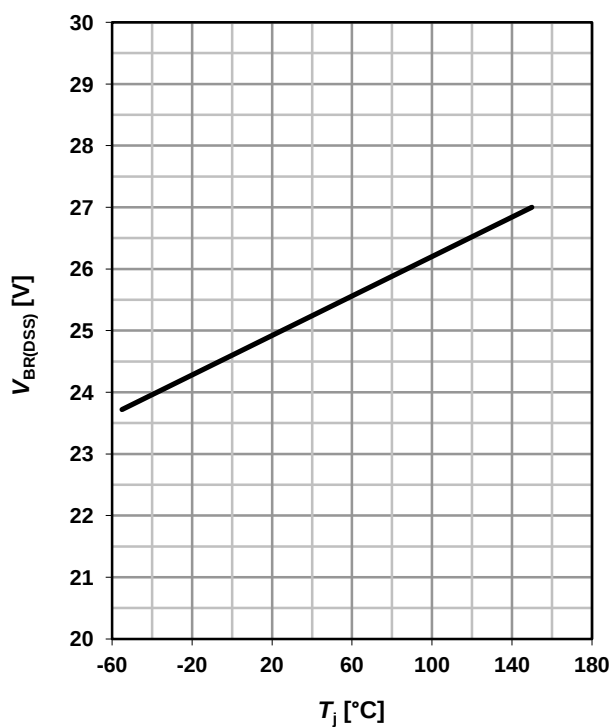
parameter: V_{DD}


26 Typ. gate charge (Q2)

 $V_{GS}=f(Q_{gate}); I_D=20\text{ A pulsed}$

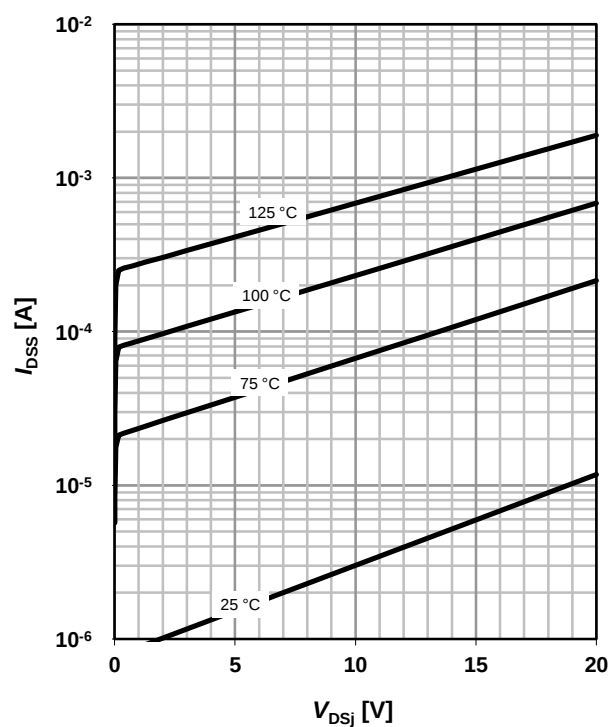
parameter: V_{DD}


27 Drain-source breakdown voltage (Q1)

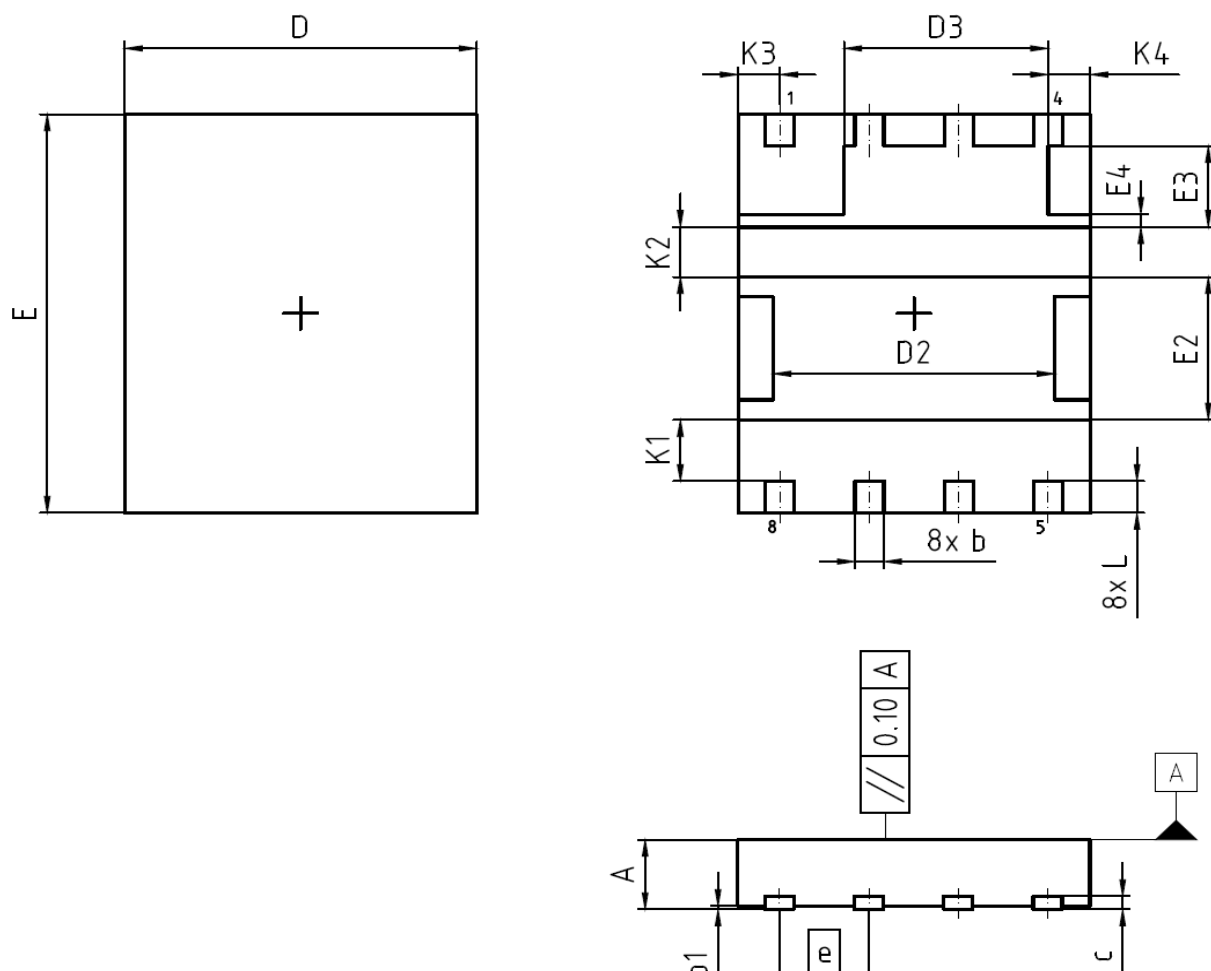
 $V_{BR(DSS)}=f(T_j); I_D=1\text{ mA}$


28 Typ. drain-source leakage current (Q2)

 $I_{DSS}=f(V_{DS}); V_{GS}=0\text{ V}$

parameter: T_j


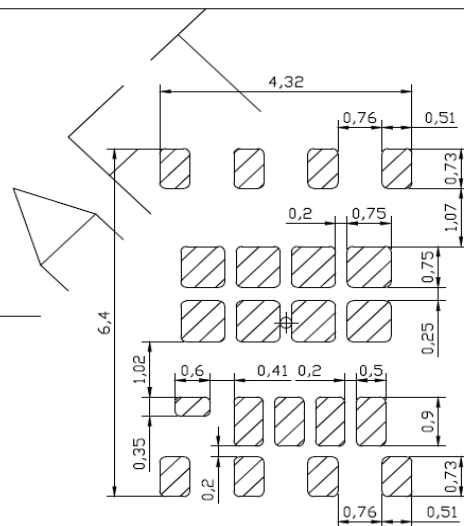
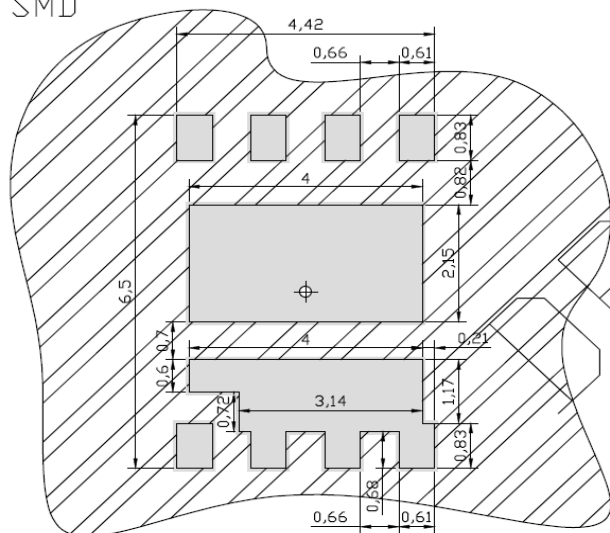
PG-TISON



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.15	0.035	0.045
b	0.31	0.51	0.012	0.020
b1	0.00	0.05	0.000	0.002
c	0.10	0.30	0.004	0.012
D	4.90	5.10	0.193	0.201
D2	3.90	4.10	0.154	0.161
D3	2.80	3.00	0.110	0.118
E	5.90	6.10	0.232	0.240
E2	2.05	2.25	0.081	0.089
E3	1.12	1.32	0.044	0.052
E4	0.10	0.30	0.004	0.012
e	1.27 (BSC)		0.05 (BSC)	
N	8		8	
L	0.38	0.58	0.015	0.023
K1	0.82	1.02	0.032	0.040
K2	0.65	0.85	0.026	0.033
K3 = K4	0.50	0.70	0.019	0.027

DOCUMENT NO. Z8B00162738	
SCALE 0 2.5 5mm	
EUROPEAN PROJECTION	
ISSUE DATE 21-09-2011	
REVISION 01	

SMD



(stencil thickness 120 μm)

■ copper

 solder mask

 stencil apertures

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Infineon Technologies AG
81726 Munich, Germany
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